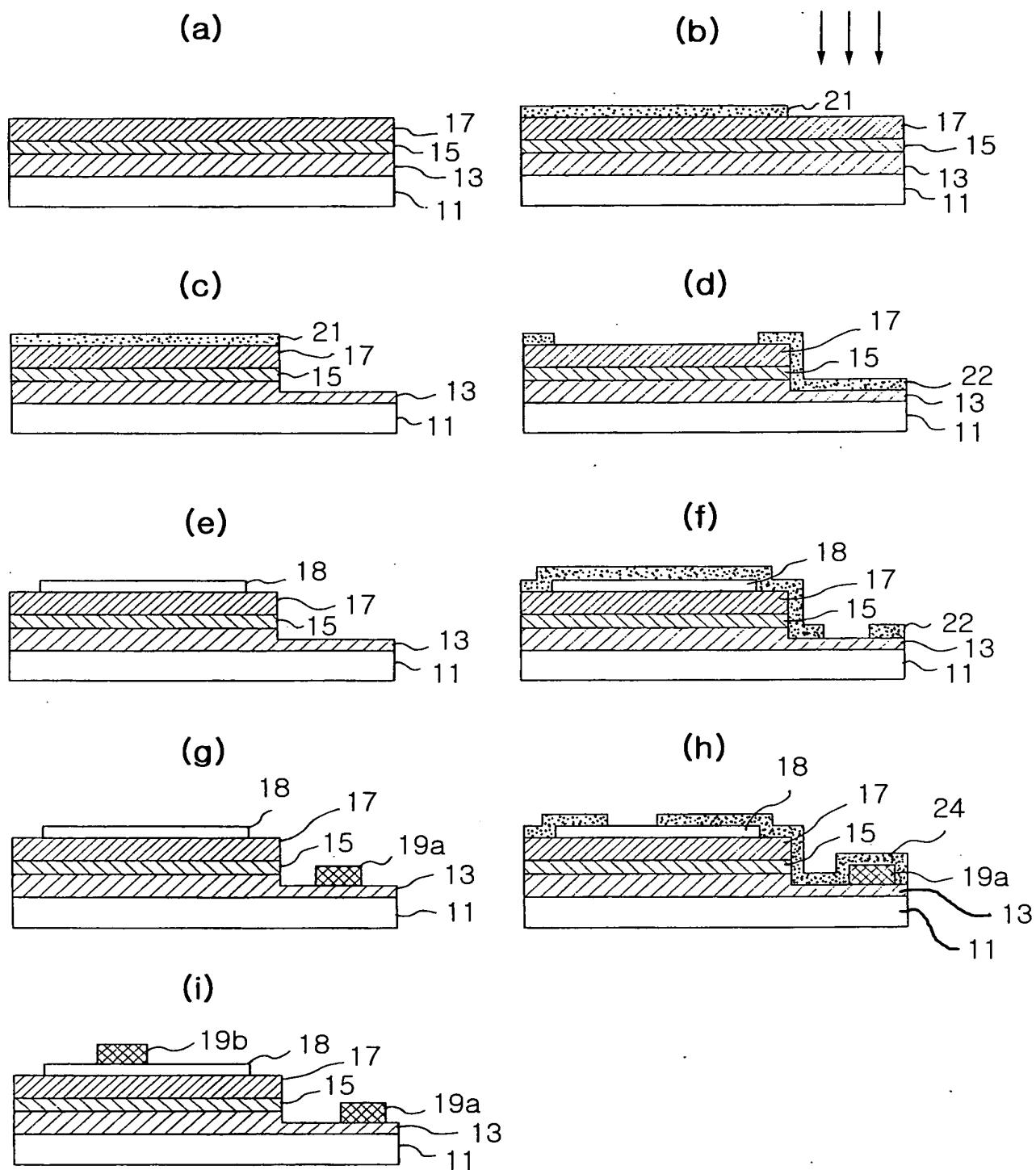


METHOD FOR MANUFACTURING GALLIUM NITRIDE-BASED SEMICONDUCTOR LIGHT
EMITTING DEVICE
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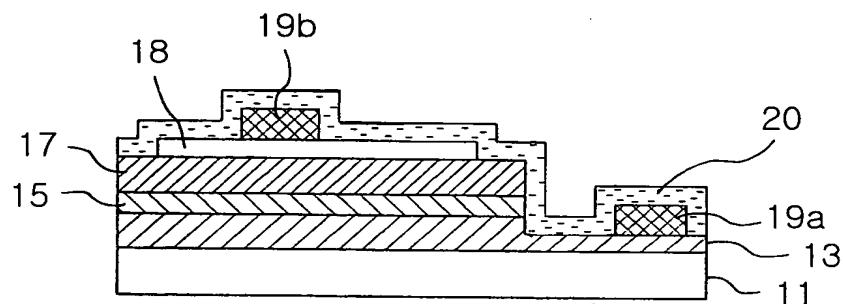
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FIG. 1

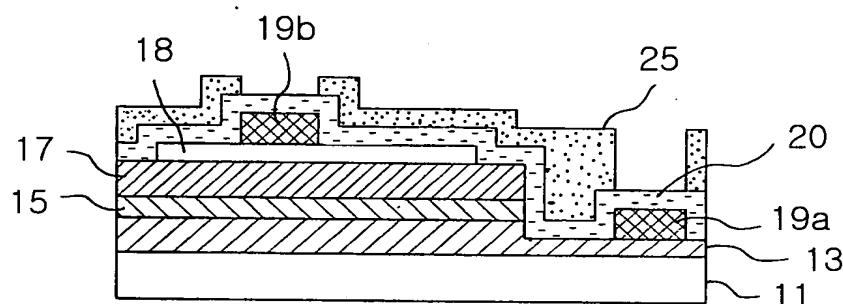
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(a)



(b)



(c)

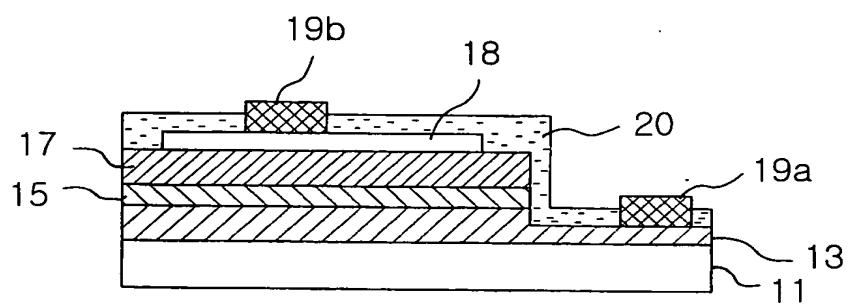


FIG. 2

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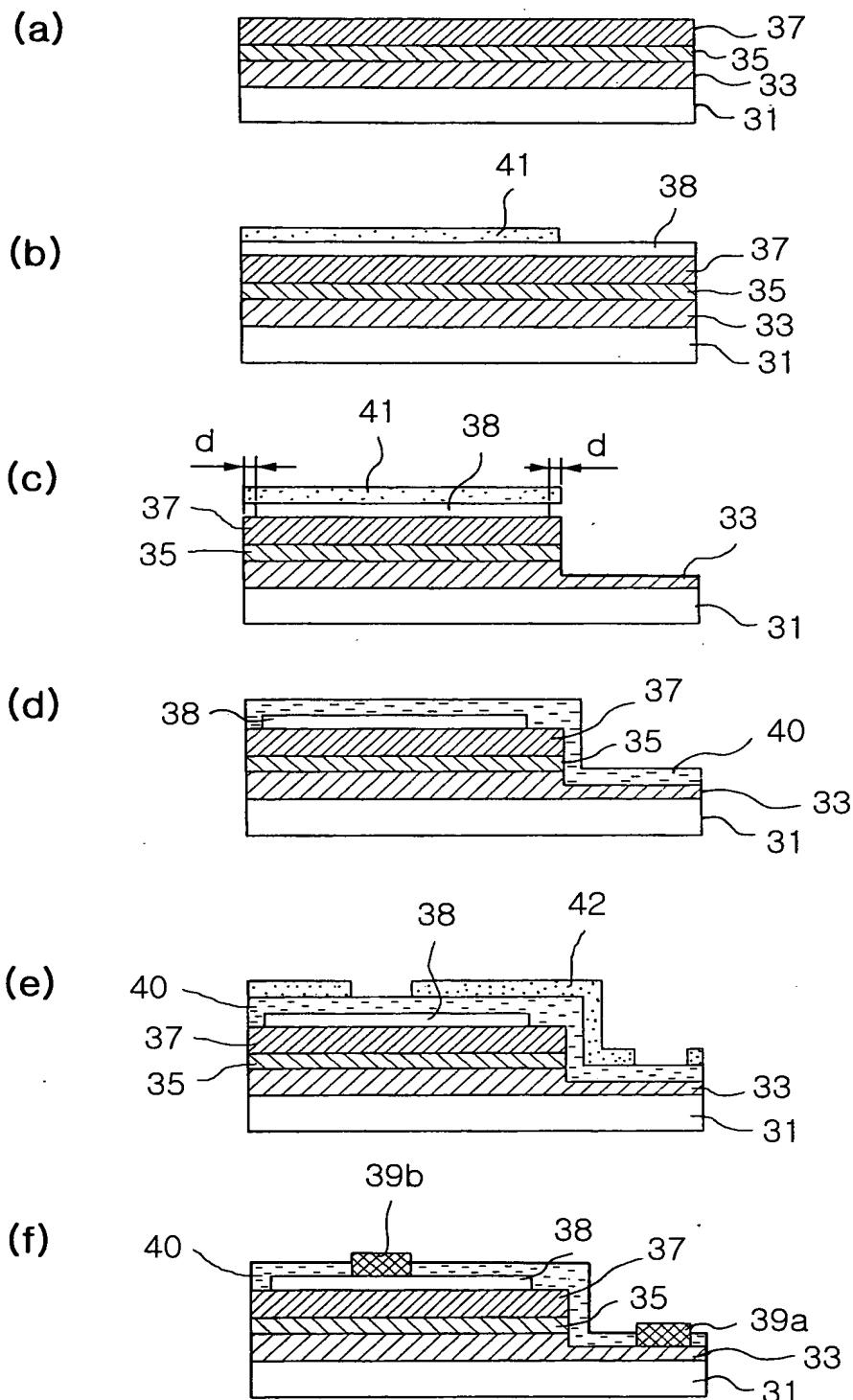


FIG. 3